

## General Description

The WSP4984 is the highest performance trench N-Channel MOSFET with extreme high cell density, which provide excellent  $R_{DS(ON)}$  and gate charge for most of the synchronous buck converter applications.

The WSP4984 meet the RoHS and Green Product requirement, 100%  $E_{AS}$  guaranteed with full function reliability approved.

## Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent  $CdV/dt$  effect decline
- 100%  $E_{AS}$  Guaranteed
- Green Device Available

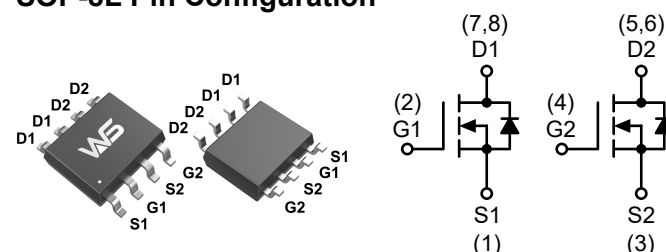
## Product Summary

$BV_{DSS}$	$R_{DS(ON)}$	$I_D$
40V	15m $\Omega$	10A

## Applications

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

## SOP-8L Pin Configuration



## Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	40	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ <sup>1</sup>	10	A
$I_D @ T_C = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ <sup>1</sup>	8	
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	50	
$P_D @ T_A = 25^\circ C$	Total Power Dissipation	2.0	W
$P_D @ T_A = 70^\circ C$	Total Power Dissipation	1.3	
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	

## Thermal Data

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient <sup>1</sup>	---	90	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case <sup>1</sup>	---	40	

**Electrical Characteristics** ( $T_J=25^{\circ}\text{C}$ , Unless Otherwise Noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V$ , $I_D=250\mu A$	40	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=10V$ , $I_D=6.6A$	---	15	20	m $\Omega$
		$V_{GS}=4.5V$ , $I_D=5.9A$	---	17.7	21	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$ , $I_D=250\mu A$	1.55	2.2	2.7	V
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=24V$ , $V_{GS}=0V$ , $T_J=25^{\circ}\text{C}$	---	---	1.0	$\mu A$
		$V_{DS}=24V$ , $V_{GS}=0V$ , $T_J=55^{\circ}\text{C}$	---	---	5.0	
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 20V$ , $V_{DS}=0V$	---	---	$\pm 100$	nA
$g_{fs}$	Forward Transconductance	$V_{DS}=15V$ , $I_D=6.6A$	---	50	---	S
$Q_g$	Total Gate Charge (4.5V)	$V_{DS}=15V$ , $V_{GS}=4.5V$ , $I_D=8.8A$	10	13.6	16	nC
$Q_{gs}$	Gate-Source Charge		3.6	4.5	5.4	
$Q_{gd}$	Gate-Drain Charge		3.8	6.4	9	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=15V$ , $V_{GEN}=10V$ , $R_G=6\Omega$ , $I_D=1A$ , $R_L=15\Omega$	---	6.4	---	ns
$T_r$	Rise Time		---	17	---	
$T_{d(off)}$	Turn-Off Delay Time		---	16.8	---	
$T_f$	Fall Time		---	29.6	---	
$C_{iss}$	Input Capacitance	$V_{DS}=15V$ , $V_{GS}=0V$ , $f=1.0\text{MHz}$	1200	1500	1950	pF
$C_{oss}$	Output Capacitance		150	250	---	
$C_{rss}$	Reverse Transfer Capacitance		---	135	---	

**Note:**

1. Surface Mounted on 1" x 1" FR4 Board.
2. Pulse test:  $PW \leq 300\mu s$  duty cycle  $\leq 2\%$ .
3. Pulse width limited by maximum junction temperature.
4. Guaranteed by design, not subject to production testing.

## Typical Characteristics

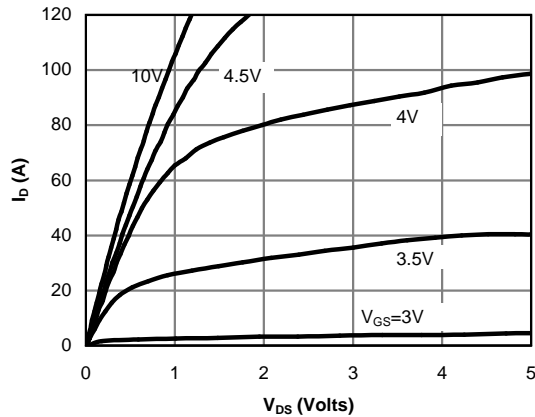


Fig 1: On-Region Characteristics (Note E)

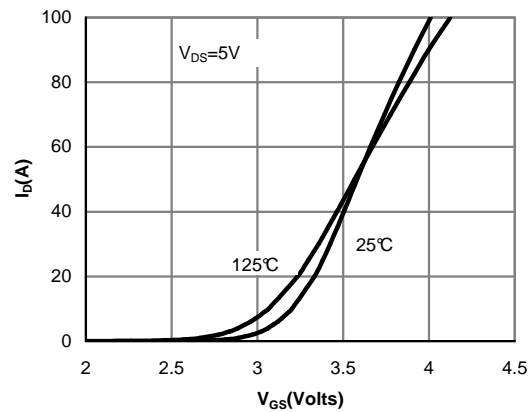


Figure 2: Transfer Characteristics (Note E)

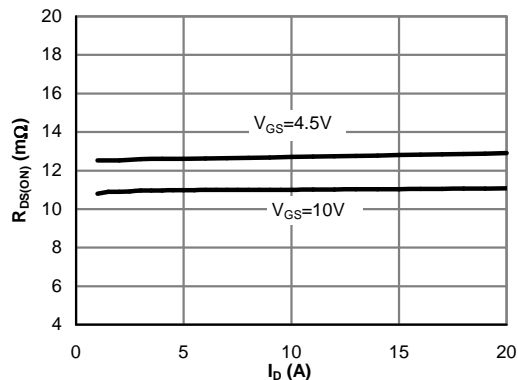


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

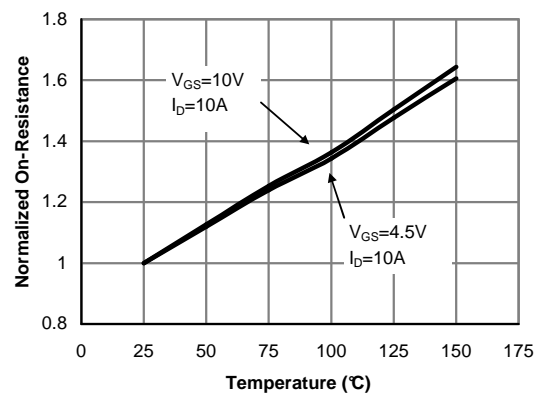


Figure 4: On-Resistance vs. Junction Temperature (Note E)

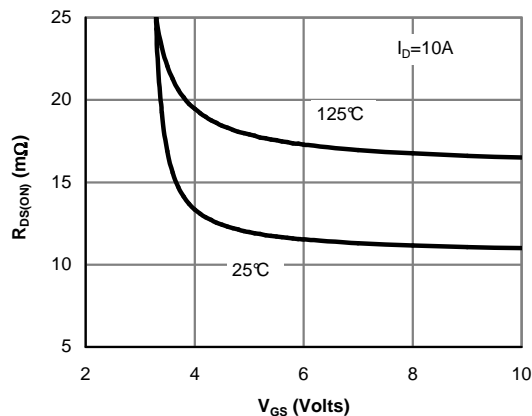


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

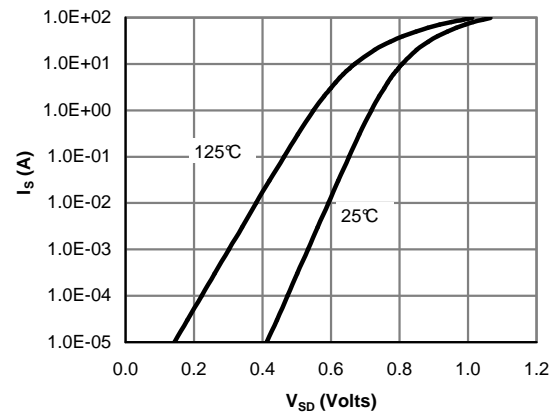


Figure 6: Body-Diode Characteristics (Note E)

## Typical Characteristics (Cont.)

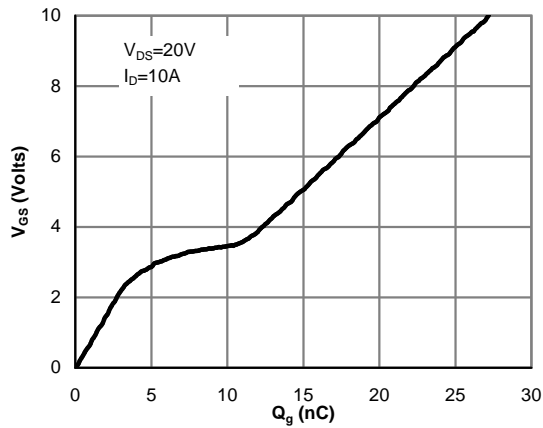


Figure 7: Gate-Charge Characteristics

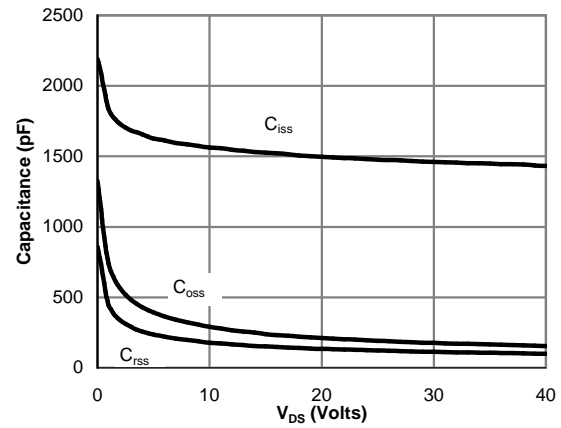


Figure 8: Capacitance Characteristics

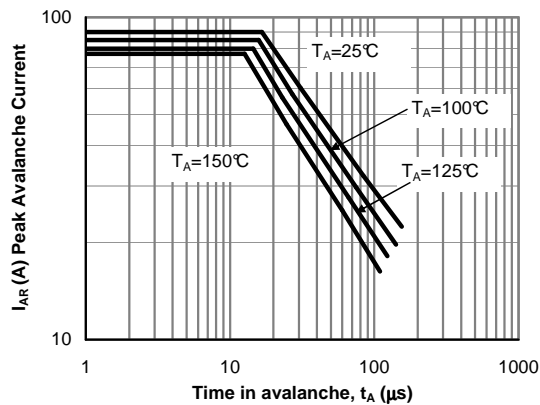


Figure 9: Single Pulse Avalanche capability (Note C)

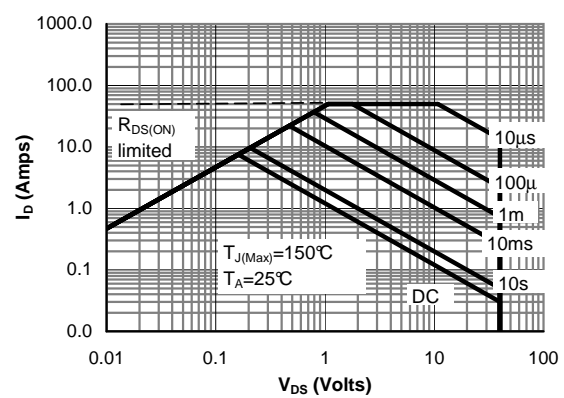


Figure 10: Maximum Forward Biased Safe Operating Area (Note F)

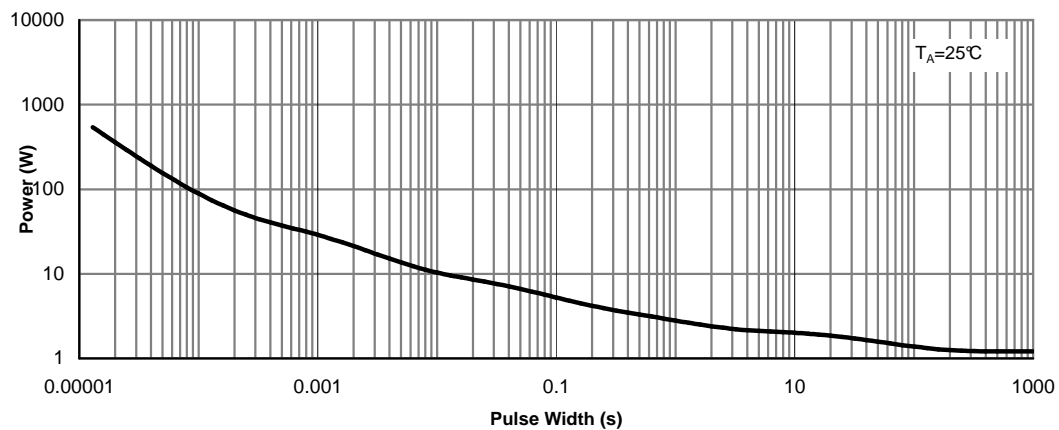


Figure 11: Single Pulse Power Rating Junction-to-Ambient (Note F)

## Typical Characteristics (Cont.)

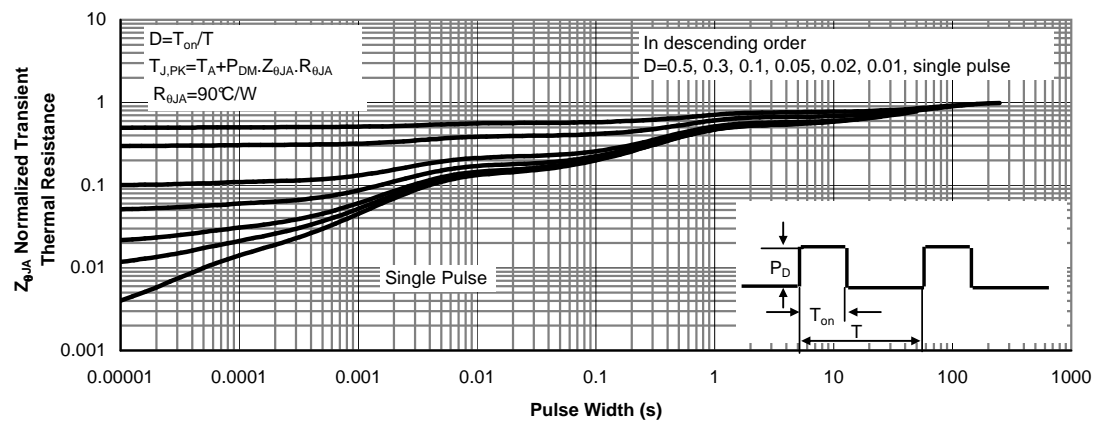
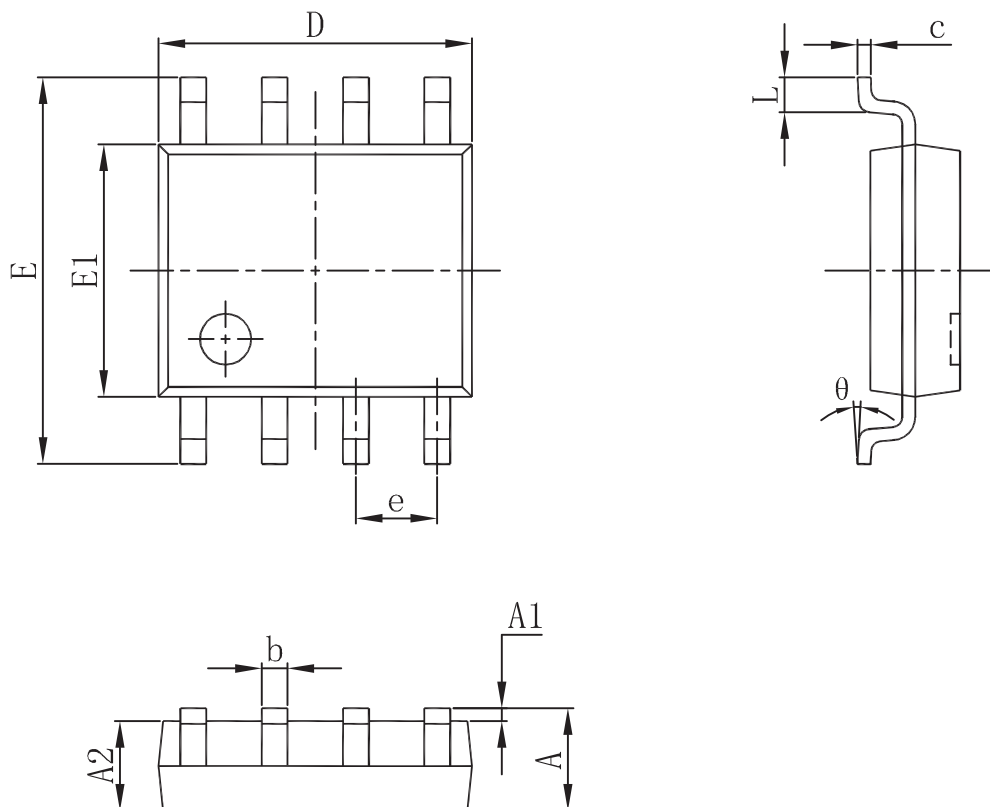


Figure 12: Normalized Maximum Transient Thermal Impedance (Note F)

## Packaging information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
e	1.270 (BSC)		0.050 (BSC)	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

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